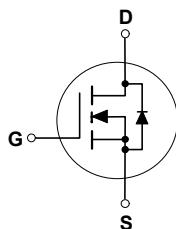
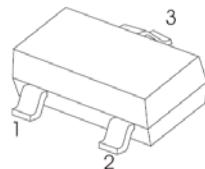


■ Features

- $V_{DS(V)} = 60V$
- $I_D = 3A$
- $R_{DS(ON)} < 80m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 95m\Omega$ ($V_{GS} = 4.5V$)

**SOT - 23**

1. GATE
2. SOURCE
3. DRAIN

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $T_a=25^\circ C$	I_D	3	A
$T_a=70^\circ C$		2.3	
Pulsed Drain Current *	$ I_{DM} $	10	
Power Dissipation $T_a=25^\circ C$	P_D	1.38	W
Linear Derating Factor		0.01	W/ $^\circ C$
Thermal Resistance.Junction-to-ambient	R_{thJA}	90	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

* 2.Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

60V N-Channel MOSFET

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$		10		μA
		$V_{DS}=48, V_{GS}=0\text{V}, T_J=70^\circ\text{C}$		25		
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=3\text{A}$		80		$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=2\text{A}$		95		
Forward Transconductance	g_{FS}	$V_{DS}=5\text{V}, I_D=3\text{A}$		5		S
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$		490	780	pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{rss}			40		
Total Gate Charge	Q_g	$V_{DS}=48\text{V}, I_D=3\text{A}, V_{GS}=4.5\text{V}$		6	10	nC
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			3		
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, I_D=1\text{A}, R_D=30\Omega, R_{GEN}=3.3\Omega$		6		ns
Turn-On Rise Time	t_r			5		
Turn-Off Delay Time	$t_{D(off)}$			16		
Turn-Off Fall Time	t_f			3		
Body Diode Reverse Recovery Time	t_{rr}	$I_S=3\text{A}, dI/dt=100\text{A}/\mu\text{s}$		25		
Body Diode Reverse Recovery Charge	Q_{rr}	$I_S=3\text{A}, dI/dt=100\text{A}/\mu\text{s}$		26		nC
Diode Forward Voltage	V_{SD}	$I_S=1.2\text{A}, V_{GS}=0\text{V}$			1.2	V

60V N-Channel MOSFET

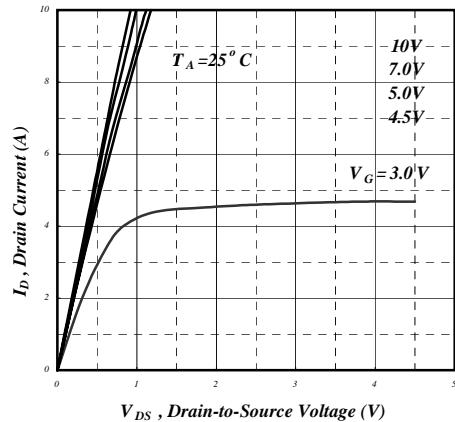


Fig 1. Typical Output Characteristics

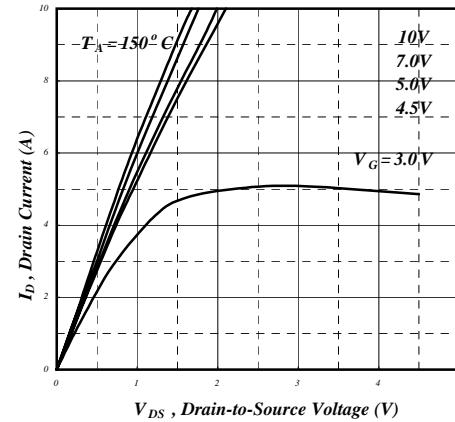


Fig 2. Typical Output Characteristics

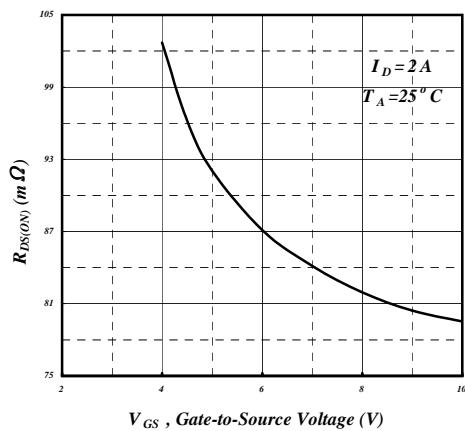


Fig 3. On-Resistance v.s. Gate Voltage

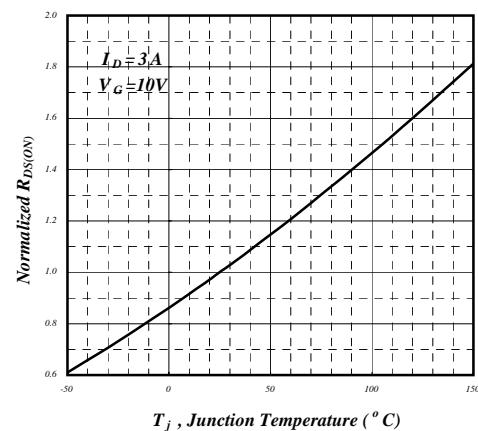


Fig 4. Normalized On-Resistance v.s. Junction Temperature

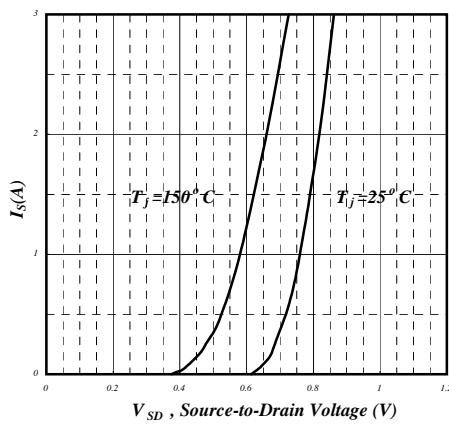


Fig 5. Forward Characteristic of Reverse Diode

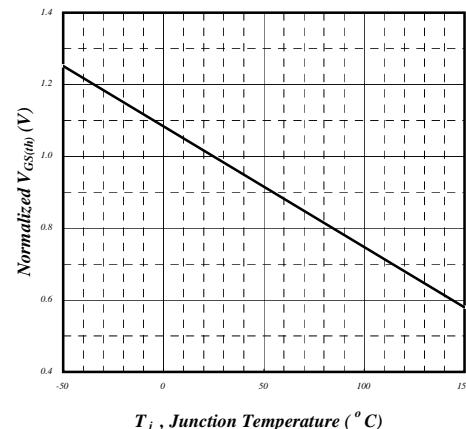


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

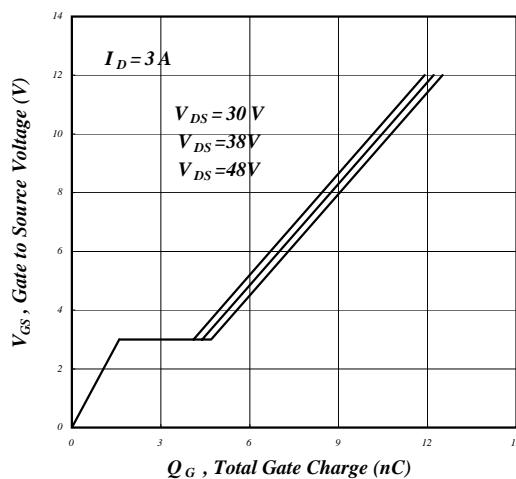


Fig 7. Gate Charge Characteristics

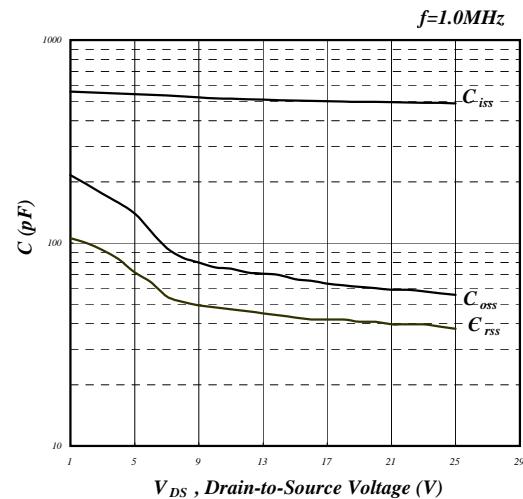


Fig 8. Typical Capacitance Characteristics

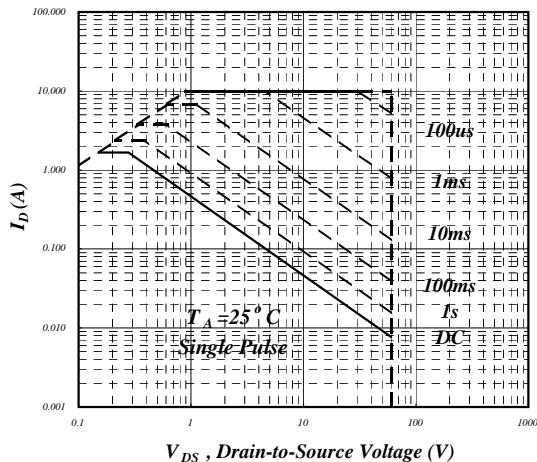


Fig 9. Maximum Safe Operating Area

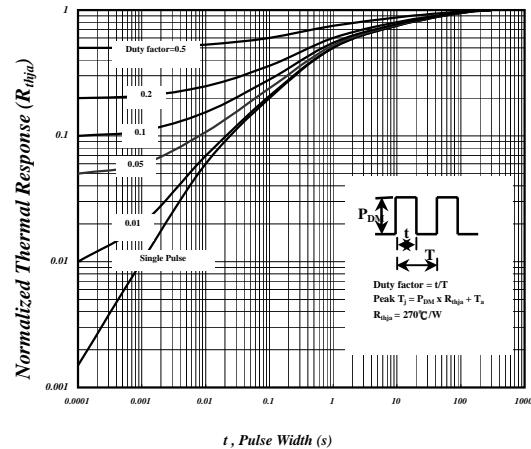
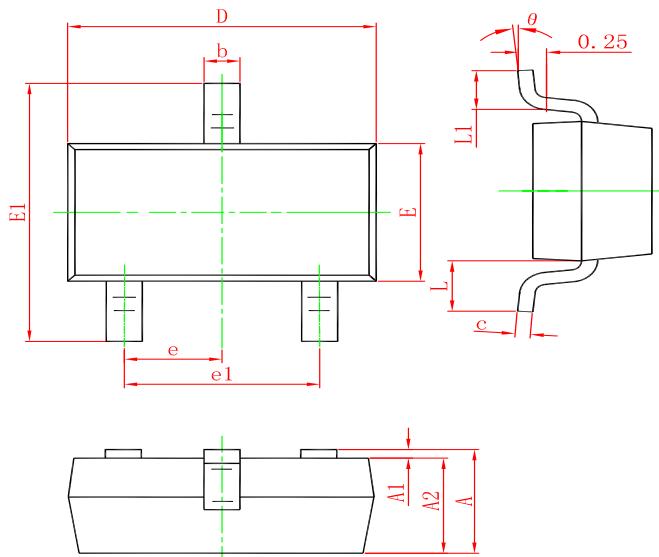
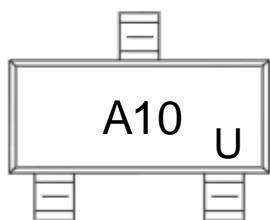


Fig 10. Effective Transient Thermal Impedance

SOT-23 PACKAGE OUTLINE DIMENSIONS

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Marking**Ordering information**

Order code	Package	Baseqty	Deliverymode
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[IPS60R360PFD7SAKMA1](#) [IPS60R600PFD7SAKMA1](#)